

NMOP-10026

Phototransistor

The NMOP-10026 is a silicon NPN phototransistor in miniature side-facing device which is molded in a water clear package with spherical top view lens. This device is specially matched to infrared emitting diode and suitable for photointerrupters and optical switches.

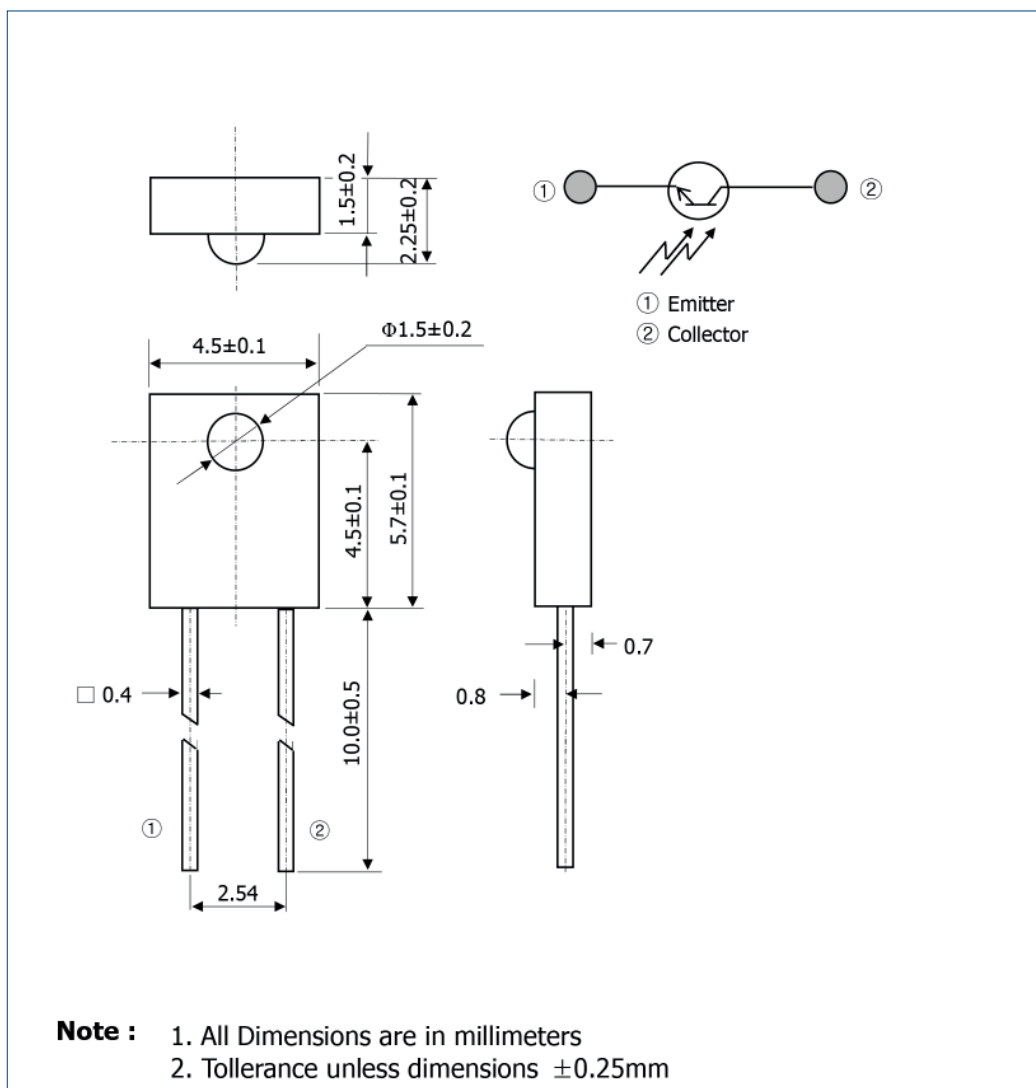
FEATURES

- Fast response time
- High sensitivity
- Low capacitance
- Lead (Pb) free product – RoHS compliant

APPLICATIONS

- Optoelectronic switch
- VCR, Video Camera
- Floppy disk driver
- Infrared applied system

Package Dimensions



NMOP-10026
MAXIMUM RATINGS
(Ta=25°C)

Item	Symbol	Rating	Unit
Collector-Emitter Voltage	VCEO	30	V
Emitter-Collector Voltage	VECO	5	V
Collector Current	IC	20	mA
Collector Power Dissipation	Pc	75	mW
Operating Temperature	Topr.	-25~ +85	° C
Storage Temperature	Tstg.	-40~+100	° C
Soldering Temperature *1	Tsol.	260	° C

*1.Soldering time ≤ 5 seconds.

ELECTRO-OPTICAL CHARACTERISTICS
(Ta=25°C)

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
Range of Spectral Bandwidth	λ		400		1,100	nm
Wavelength of Peak Sensitivity	λ_p			940		nm
Collector-Emitter Breakdown Voltage	BVCEO	IC=100 μ A Ee=0mW/cm ²	30			V
Emitter-Collector Breakdown Voltage	BVECO	IE=100 μ A Ee=0mW/cm ²	5			V
Collector-Emitter Saturation Voltage	BVCE(sat)	IC=2mA Ee=1mW/cm ²			0.4	V
Collector Dark Current	ICEO	VCE=20V Ee=1mW/cm ²			100	nA
On State Collector Current	IC(on)	VCE=5V Ee=0.555mW/cm ²	0.8		5.0	mA
Rise/Fall time	tr/tf	VCE=5V IC=1mA,RL=1K Ω		15/15		μ S